

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	US-5248885-\$.DID. OR US-6274882-\$.DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/08/16 15:52
L2	22	US-6037614-\$.DID. OR US-5959340-\$.DID. OR US-5650635-\$.DID. OR US-5455421-\$.DID. OR US-5016073-\$.DID. OR US-4970567-\$.DID. OR US-1516627-\$.DID. OR JP- 07051978-\$.DID. OR US- 5358791-\$.DID. OR WO- 9605621-\$.DID. OR JP- 2000269537-\$.DID. OR JP- 62257773-\$.DID. OR JP- 5160429-\$.DID. OR JP- 6196745-\$.DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/08/16 15:54
L3	33	infrared adj sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and infrared adj sensor and ("257". clas. "438".clas.)	USPAT	OR	OFF	2009/08/16 16:02
L4	31	infrared adj sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and infrared adj sensor and ("257". clas. "438".clas.) and @ay<="2006"	USPAT	OR	OFF	2009/08/16 16:03

L5	13	infrared adj sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and infrared adj sensor and ("257". clas. "438". clas.) and @ay<="2006" and plurality with layer	USPAT	OR	OFF	2009/08/16 16:03
L6	27	infrared adj sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and infrared adj sensor and ("257". clas. "438". clas.) and @ay<="2006" and plurality with layer	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/16 16:03
L7	30	infrared adj sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and infrared adj sensor and ("257". clas. "438". clas.) and @ay<="2006" and plurality with layer	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 16:03
L8	14	ueno.in. and "InSb"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 16:21
L9	14	ueno.in. and "InSb" and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 16:21
L10	7	(seventh eighth) adj layer and infrared adj sensor and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 16:48
L11	7	(seventh eighth ninth) adj layer and infrared adj sensor and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 16:48
L12	448	multilayer and infrared adj sensor and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 16:49
L13	31	multilayer and "InSb" and infrared adj sensor and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 16:49
L14	17	multilayer and "InSb" and p-type and n-type and infrared adj sensor and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 16:50

L15	11	multilayer and "InSb" and "Sn" and "Zn" and p-type and n-type and infrared adj sensor and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 16:52
L16	1	("Sn" and "Zn") with (p-type and n-type) and infrared adj sensor and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 17:00
L17	4	"Sn" with (n-type) and infrared adj sensor and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 17:03
L18	3	"571287".ap.	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 18:13
L19	0	multilayer and "InSb" and p-type and n-type and infrared adj sensor and higher adj carrier adj density and @ay<="2006"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 18:25
L20	3	multilayer and ("Te" "Se") with n-type and infrared adj sensor and @ay<="2006""	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2009/08/16 18:31
S1	3	"571287".ap.	US-PGPUB; USPAT	OR	OFF	2009/03/12 17:45
S2	7823	semiconductor and sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and hybrid	US-PGPUB; USPAT	OR	OFF	2009/03/12 17:48
S3	4418	semiconductor and sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and hybrid	USPAT	OR	OFF	2009/03/12 17:48
S4	1615	semiconductor and sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and hybrid and ("257".clas. "438".clas.)	USPAT	OR	OFF	2009/03/12 17:48

S5	16	semiconductor and sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and hybrid and infrared adj sensor and ("257".clas "438".clas)	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 12:46
S6	4	semiconductor and sensor and indium and antimony and detect\$3 and infrared adj radiation and signal and an integrat\$ adj circuit and package and hybrid and infrared adj sensor and ("257".clas. "438".clas.) and @ay<="2004"	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 12:47
S7	448	infrared adj sensor and ("257".clas. "438".clas.) and @ay<="2004"	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 12:49
S8	18	infrared adj sensor and substrate and stack\$3 and plurality with (semiconduct \$3 adj (layer material film)) and ("257".clas. "438".clas.) and @ay<="2004"	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 12:50
S9	0	infrared adj sensor and substrate and stack\$3 and plurality with (semiconduct \$3 adj (layer material film)) and ("257".clas. "438".clas.) and @ay<="2004" and (sixth seventh) adj coumpound	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 12:51
S10	13	infrared adj sensor and substrate and stack\$3 and plurality with (semiconduct \$3 adj (layer material film)) and ("257".clas. "438".clas.) and @ay<="2004" and p-type and n-type	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 12:52
S11	21	infrared adj sensor and substrate and stack\$3 and plurality and (semiconduct \$3 adj (layer material film)) and ("257".clas. "438".clas.) and @ay<="2004" and p-type and n-type	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 13:02

S12	21	infrared adj sensor and substrate and stack\$3 and plurality and (semiconduct\$3 adj (layer material film)) and ("257".clas. "438".clas.) and @ay<="2004" and p-type and n-type	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 13:02
S13	7	infrared adj sensor and substrate and stack\$3 and plurality and (semiconduct\$3 adj (layer material film)) and ("257".clas. "438".clas.) and @ay<="2004" and p-type and n-type and ("InSb" "InAsSb" "GaInSb")	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 13:40
S14	7	infrared adj sensor and substrate and stack\$3 and plurality and (semiconduct\$3 adj (layer material film)) and @ay<="2004" and p-type and n-type and ("InSb" "InAsSb" "GaInSb")	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 13:42
S15	12	infrared adj sensor and substrate and (semiconduct\$3 adj (layer material film)) and @ay<="2004" and p-type and n-type and ("InSb" "InAsSb" "GaInSb")	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 13:42
S16	2	infrared adj sensor and substrate and @ay<="2004" and p-type and n-type and ("InSb" "InAsSb" and "GaInSb")	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 13:42
S18	12	infrared adj sensor and substrate and (semiconduct\$3 adj (layer material film)) and ("257".clas. "438".clas.) and @ay<="2004" and p-type and n-type and ("InSb" "InAsSb" "GaInSb")	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 15:28

S19	2	infrared adj sensor and substrate and(semiconduct \$3 adj (layer material film)) and ("257" clas "438" clas) and @ay<="2004" and p-type and n-type and ("InSb" and "InAsSb" and "GalnSb")	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 15:30
S20	4	infrared adj sensor and substrate and p-type and n-type and ("InSb" and "InAsSb" and "GalnSb")	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 15:33
S21	108	infrared adj sensor and antimony and indium	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 15:34
S24	54	infrared adj sensor and antimony and indium and @ay<="2003"	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 15:35
S25	8	infrared adj sensor and antimony and indium and @ay<="2003" and stack \$3	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 15:35
S26	7	infrared adj sensor and "In" and "Sb" and @ay<="2003" and stack \$3	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/04 15:36
S27	22	US-6037614-\$.DID. OR US-5959340-\$.DID. OR US-5650635-\$.DID. OR US-5455421-\$.DID. OR US-5016073-\$.DID. OR US-4970567-\$.DID. OR US-1516627-\$.DID. OR JP-07051978-\$.DID. OR US-5358791-\$.DID. OR WO-9605621-\$.DID. OR JP-2000269537-\$.DID. OR JP-62257773-\$.DID. OR JP-5160429-\$.DID. OR JP-6196745-\$.DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/08/04 15:38
S28	23	("3364084" "4207122" "4368098" "4404265" "4607272" "4630279" "4720309" "4793872" "4874438" "4897149" "4902356" "4952811" "5232869").PN. OR ("5650635") URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/08/04 15:39
S29	42	shigenaka in.	USPAT	OR	OFF	2009/08/12 16:03

S30	0	shigenaka.in. and optical adj semiconductor	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/12 16:03
S31	0	shigenaka.in. and substrate and "InAsSb"	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/12 16:03
S32	0	Keitaro.in. and substrate and "InAsSb"	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2009/08/12 16:04

8/ 16/ 2009 7:36:55 PM

C:\Documents and Settings\tgreen1\My Documents\EAST\Workspaces\10571287.wsp